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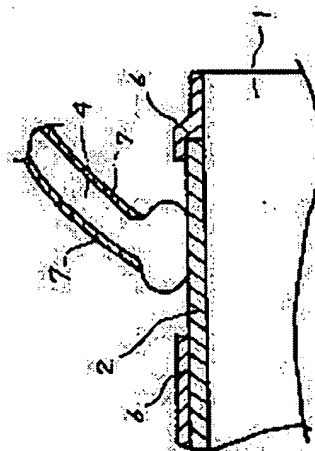
(72)Inventor : YOSHIDA TORU
MATSUI KIYOSHI

(54) RESIN MOLDED SEMICONDUCTOR DEVICE

(57)Abstract:

PURPOSE: To improve reliability on the damp-proofness of a resin molded semiconductor device by using a small-gage wire in which the surface of a gold wire is coated with aluminum.

CONSTITUTION: An aluminum electrode 2 and an silicon nitride film 6 are formed on a semiconductor base body 1, and the silicon nitride film 6 in a bonding section is removed. Such a semiconductor element is fixed on a lead frame, and a small-gage wire in which aluminum 7 is evaporated on the surface of a gold wire 4 is bonded, and molded with a resin. Consequently, when moisture intruding to the interface between the resin and the lead frame from the outside reaches to the interface between the resin and the gold wire 4 coated with aluminum 7, aluminum 7 dissolves, and moisture contains a saturated quantity of aluminum ions. Accordingly, when moisture further reaches to the aluminum electrode 2, the aluminum electrode 2 is not corroded because aluminum is brought previously to a sufficiently saturated state.



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